# **Application Note**

SI-3000ZD Series

1<sup>st</sup> Edition February 2010

SANKEN ELECTRIC CO., LTD.

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### 1. General Information

The SI-3000ZD is a series regulator IC using a hyposaturation type PNP bipolar transistor in the power section; it can be used with the low difference of input/output voltages and rated 3A. It is provided with an ON/OFF terminal which operates in Active High mode and the current consumption of circuits at OFF time is zero.

#### • 1-1 Features

- Output current 1A

Output current is 3A at maximum with the outline of TO263-5.

- Hyposaturation ( $V_{dif} = 0.6V \text{max} / \text{Io} = 3A$ )

It can be designed with low difference of input/output voltages.

- ON/OFF function

The ON/OFF terminal which can be directly controlled by TTL logic signals is provided.

- Low current consumption

Current consumption of circuits at OFF time is zero.

Dark currents at no load are 1.5mA at maximum.

- High ripple attenuation ratio

75dB (SI-3050KD): F = 100 - 120kHz)

- Built-in overcurrent protection

The automatic restoration and foldback type overcurrent protection circuit is built in.

#### • 1-2 Application

For on-board local power supplies, power supplies for OA equipment, stabilization of secondary output voltage of regulator and power supply for communication equipment

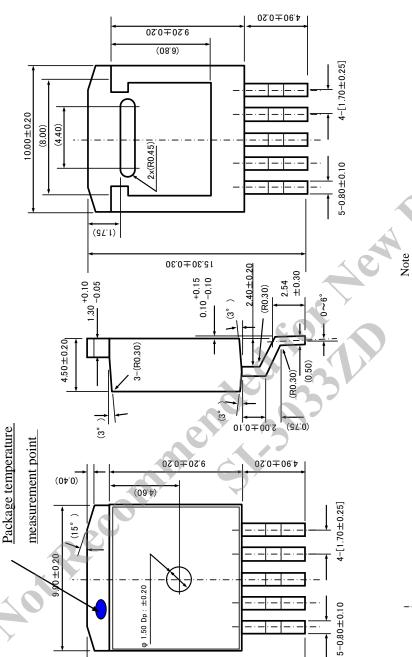
#### ● 1-3 Type

- Type: Semiconductor integrated circuits (monolithic IC)
- Structure: Resin molding type (transfer molding)

# 2. Specification

#### • 2-1 Package Information

Unit: mm



Figures in parentheses ( ) are shown only

Dimensions do not include molding burr.

Figures in parentheses [ ] are dimensions

3

for reference.

Backside bumps: 0.8 mm at maximum

**€ €** 

after lead forming.

Products Weight: Approx.1.48g

The stem part has same potential as No. 3 pin (GND).

15.30±0.30

#### Pin assignment

- 1. Vc (on/off)
- 2. VIN
- 3. GND
- 4. Vout
- 5. ADJ

#### • 2-2 Ratings

#### 2-2-1 Absolute Maximum Ratings

Ta=25°C

Parameter	Symbol	Rafings	Unit	
DIC Input Voltage	Vin'1	10	V	
Output Control Terminal Voltage	Vc	£	V	
DC Output Current	lo't	3.0	A	
Power Dissipation	P0 <sup>'3</sup>	3	W	
Junction Temperature	T <sub>1</sub>	-30 to +125	*C	
Operating Ambient Temperature	Top	-30 to +85	10	
Storage Temperature	Trap	-40 to +125	*0	
Thermal Resistance (Junction to Ambient Air)	Ø)-a	33.3	*C/W	
Thermal Resistance (Junction to Case) 6-c		3	'C/W	

#### 2-2-2 Recommended Conditions

Parameter	Symbol	Ratings	Uest	Ramarks
Input Voltage	Viv	77 to 671	٧	
Output Current	lo lo	5 to 3	A	67
Operating Ambient Temperature	Topos	-20 to +85	*C	03
Operating Junction Temperature	Two	-20 to +100	10	
Output Voltage Variable Range	VOADU	1.2 to 5	V	Doly for BI-3011ZD. Refer to the block diagram.

<sup>\*1:</sup> Viv (max) and to (max) are restricted by the relation  $P_D = (Viv + Vo) \times Io$ 

#### 2-2-3 Electrical Characteristics (SI-3011ZD, SI-3033ZD) Ta=25°C, Vc = 2V if without special instruction

					Rai	tings				
Parameter	Symbol	SI-3011ZD (Variable type)			SI-3033ZD			Unit		
	2011	min.	typ.	max.	min.	typ.	max.			
Output Vo	Itage	Vo (VADJ)	1.078	1.100	1.122	3.234	3.300	3.366	V	
(Reference Voltage VADJ for SI-3011ZD)		Conditions	VIN=Vo+1V, Io=10mA			Vin=5V, lo=10mA			1 ,	
Line Regulation	ΔVOLINE			10:			10	mV		
	Conditions	Vin=3.3 to 5V, lo=10mA (Vo=2.5V)			V	mv				
Load Regulation	ulation	ΔVOLOAD			40			40	mV	
	Conditions	Vin=3.3V, lo=0 to 3A (Vo=2.5V)		VIN=5V, Io=0 to 3A			- IIIV			
Dropout Voltage	VDIF		( )	0.6			0.6	V		
	Conditions	lo=3A (Vo=2.5V)		lo=3A			7 *			
Quiescent Circuit Current	Direction Common	lq .		1	1.5	3	1	1.5	m.A	
	Circuit Guirent	Conditions	Vin=Vo+1V, lo=0A, Vc=2V			VIN=5V, Io=0A, Vc=2V			IIIA	
Circuit Current at Output OFF	rropt at Output OEE	lq (OFF)			1	6		1	μА	
Circuit Current at Output OFF		Conditions		VIN=Vo+1V, Vc=0V		Vin=5V, Vc=0V		μΑ		
Temperature Coefficient of Output Voltage		ΔVα/ΔΤα		±0.3			±0.3	ř .	mV/	
		Conditions	Tj=0 to 100°C			Tj=0 to 100°C			Till V	
Ripple Rejection		RREJ		60			60		dB	
		Conditions	VIN=V0+1V, f=100 to 120Hz, Io=0.1A VIN=5V, f=100 to 120Hz, Io=0.1A		=0.1A	UB				
Overcurrent Protection Starting Current*2		IS1	3.2			3.2			A	
		Conditions	ViN=Vo+1V		ViN=5V			^		
0	Control Voltage (Output ON) 3	Vc, IH	2			2			V	
C	Control Voltage (Output OFF)*3	Vc, IL			0.8			0.8		
	Control Current(Output ON)	lc, fH			100			100	μА	
Terminal		Conditions	Vc=2.7V			Vc=2.7V			μΑ	
0	Control Current(Output OFF)	lc, IL	-5	0		-5	0		μА	
	1/3.4// 3.4	Conditions		Vc=0V			Vc=0V	•==	μА	

<sup>\*1:</sup> Set the input voltage to 2.4V or higher when setting the output voltage to 2.0V or lower.

- \*2: Is1 is specified at the -5% drop point of output voltage Vo under the condition of Output Voltage parameter.
- \*3: Output is OFF when the output control terminal (Vc terminal) is open. Each input level is equivalent to LS-TTL level. Therefore, the device can be driven directly by LS-TTLs.
- \*4: These products cannot be used for the following applications because the built-in foldback-type overcurrent protection may cause errors during start-up stage.
- (1) Constant current load (2) Positive and negative power supply (3) Series-connected power supply (4) Vo adjustment by raising ground voltage

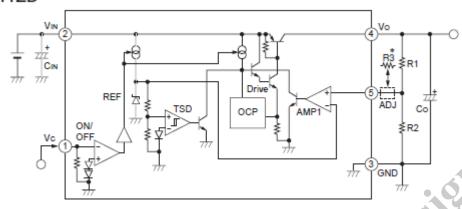
<sup>\*2.</sup> Set the input voltage to 2.4V or higher when setting the output voltage to 2.0V or lower (SI-3011ZD).

<sup>\*1:</sup>  $V_{IN}$  (max) and Io (max) are restricted by the relation  $P_D = (V_{IN} - V_O) \times I_O$ .

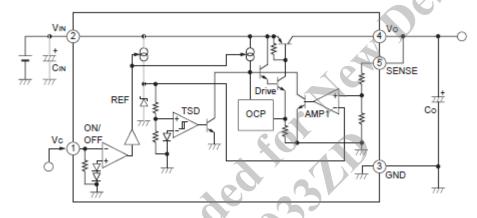
<sup>\*2:</sup> Set the input voltage to 2.4V or higher when setting the output voltage to 2.0V or lower (SI-3011ZD).

### • 2-3 Circuit Diagram

### SI-3011ZD



#### SI-3033ZD



C<sub>IN</sub>: Input Capacitor (around 10μF)

C<sub>o</sub>: Output Capacitor (over 47µF)

In the SI-3000ZD, if capacitors with low ESR such as ceramic capacitors are used, the output voltage may oscillate.

#### R1, R2: resistors for setting output voltages

Output voltages can be set by connecting R1 and R2 as shown in the above figure.

R2:  $10k\Omega$  or  $11k\Omega$  are recommended.

$$R1 = (V_O - V_{ADJ}) / (V_{ADJ} / R2)$$

In the case that  $Vo \le 1.8V$  is set, R3 should be inserted.

 $10 \text{ k}\Omega$  is recommended for R3.

# 3. Operational Description

#### • 3-1 Voltage Control

In the SI-3000ZD series, the driving circuit is controlled by comparing the reference voltage with the ADJ terminal voltage (voltage divided by Vo detection resistor in fixed output products) to stabilize the output voltage by varying the voltage between the emitter and collector of a main PNP power transistor. The product of voltage between emitter and collector and the output current at this moment is consumed as heat.

#### • 3-2 Overcurrent Protection

#### 3-2-1 Overcurrent Protection Characterization for SI-3011ZD and SI-3033ZD

The foldback type overcurrent protection function is provided in the SI-3011ZD and SI-3033ZD. After operation of the overcurrent protection function, if the load resistance decreases and the output voltage drops, the output current of products is squeezed to reduce the increase of loss. However, in the case of the foldback type overcurrent protection function, since current limiting is also made at start-up, the function may not be used for the following applications, as it may cause a start-up error.

- (1) Constant current loads
- (2) Plus/minus power supply

Output voltage

(3) DC power supply

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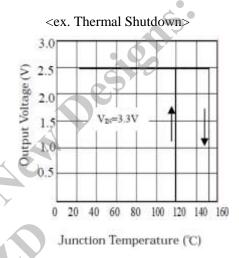
(4) Output voltage adjustment by grounding-up

<ex. Foldback Overcurrent Protection>

-Output Current

#### • 3-3 Thermal Shutdown

This IC is provided with the overheat protection circuit which detects the semiconductor junction temperature of the IC to limit the driving current, when the junction temperature exceeds the set value (around  $150^{\circ}$ C). Since the minimum operating temperature of the overheat protection circuit is  $130^{\circ}$ C, the thermal design of Tj <125°C is required. Since the hysteresis of around  $30^{\circ}$ C is provided for the overheat protection, when the junction temperature falls below the set temperature, the operation is automatically restored.



\*Note for thermal shutdown characteristic

This circuit protects the IC against overheat resulting from the instantaneous short circuit, but it should be noted that this function does not assure the operation including reliability in the state that overheat continues due to long time short circuit.

### 4. Cautions

#### • 4-1 External Components

#### 4-1-1 Input Capacitor CIN

The input capacitor is required to eliminate noise and stabilize the operation and values of  $0.47\mu F$  -  $22\mu F$  are recommended. Any of ceramic capacitors or electrolytic ones may be used for the input capacitor.

#### 4-1-2 Output Capacitor Co

In the output capacitor Co, larger capacitance than the recommended value is required for phase compensation. Equivalent series resistance values (ESR) of capacitors are limited, and depending on products, therefore the type of recommended capacitors is limited.

#### - Recommended values: $2\Omega > ESR > 0.2\Omega$

<u>It is recommended to use electrolytic capacitors.</u> When capacitors with extremely high ESR such as ceramic capacitors, functional polymer capacitors etc., are used, phase margin is decreased, possibly causing the oscillation of output voltage.

#### 4-1-3 Reverse bias protection diode D1

In the case of falling-down of the input voltage, it is recommended to insert a protection diode D1 against the reverse bias between input and output. However, in the case of setting the Vout < 3.3V or lower, D1 is not required including the case of reverse bias. In order to select a suitable D1, it should be taken into consideration that the diode has adequate forward current withstand voltage against the instantaneous discharge of energy stored in Cout.

The permissible value of the forward current per unit time of diode is specified in  $I_{FSM}$  (A) and in the case of our diode, it is specified at 50Hz half wave (10ms), but it should be noted that different companies may specify different times. The selection of diode should be made by converting the specified time into the actual discharging time so as to meet the required  $I_{FSM}$  (A). The discharging time of Co is normally shorter than 1ms, but it is recommended to do the conversion with 1ms in consideration of margin.

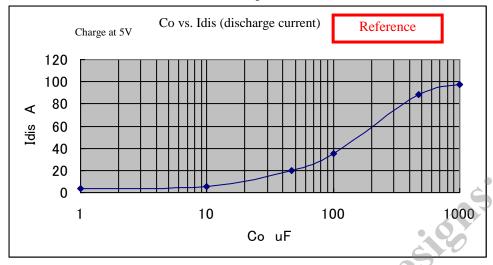
For conversion into I<sub>FSM</sub>, calculation should be made by using the equations (1) and (2).

$$\left(\frac{I_{FSM}}{\sqrt{2}}\right)^2 * t1 = X$$
 --- (1) As for  $I_{FSM}$ , please refer to the catalog of each company.

t1 = specified time in catalog of each company

Converted IFSM = 
$$\sqrt{\frac{2*X}{t^2}}$$
 --- (2) t2: converted time (discharging time of Co)





On the assumption of Cout =  $470\mu$ F,  $I_{FSM}$  of around 90A or more (in 1ms time period) is required and according to our specifications of diode,  $I_{FSM}$  is specified for 10ms, therefore the diode of 30A has the tolerated dose of 94.8A (in 1ms) to prove that it is usable.

#### • 4-2 Pattern Design Notes

#### 4-2-1 Input / Output Capacitor

The input capacitor C1 and the output capacitor C2 should be connected to the IC as close as possible. If the rectifying capacitor for AC rectifier circuit is on the input side, it can be used as an input capacitor. However, if it is no close to the IC, the input capacitor should be connected in addition to the rectifying capacitor.

#### 4-2-2 ADJ Terminal (Output Voltage Set-up for SI-3011ZD)

The SI - 3011ZD is a variable regulator and the output voltage can be arbitrarily set by using the feedback detection terminal (ADJ terminal) for controlling the output voltage.

The output voltage set-up is achieved by connecting R1 and R2.

SI-3011ZD: it should be set in a manner that  $I_{ADJ}$  is around 100 $\mu A$ .

R1, R2 and output voltage can be obtained by the following equations:

$$I_{ADJ} = V_{ADJ}/R2$$
  $\bigg(*V_{ADJ} = 1.1V \pm 2\% \text{ (SI-3011ZD)}, R2 = 10k\Omega \text{ or } 11k\Omega \text{ recommended}\bigg)$ 

$$R1 = \left(Vo\text{-}V_{ADJ}\right) / I_{ADJ} \qquad \qquad R2 = V_{ADJ} / I_{ADJ}$$
 
$$Vout = R1 \times \left(V_{ADJ} / R2\right) + V_{ADJ}$$

# 5. Applications

#### • 5-1 Output ON/OFF Control

The ON/OFF control of output can be made by directly applying voltage to No. 1 Vc terminal. When the Vc terminal is open, the operation is in OFF. The Vc terminal is in OFF below 0.8V and in ON at above 2V.

#### • 5-2 Thermal Design

Calculation of heat dissipation

Heat generation of the surface mounting IC is generally dependent on size, material and copper foil area of the mounted printed circuit board. Full attention should be paid to heat dissipation and adequate margin be taken into consideration at thermal design. In order to enhance the heat dissipation effect, it is recommended to enlarge the copper foil area connected to the stem part on the back side of the product. The copper foil area of the printed circuit board significantly affects the heat dissipation effect.

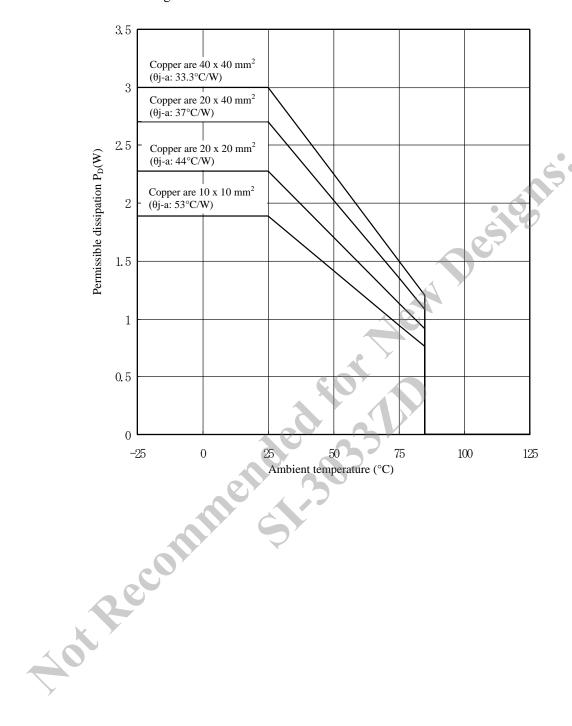
As the junction temperature Tj (MAX) is a product-specific value, it must be observed strictly. For this purpose, heat sink design (thermal resistance of board) which is appropriate for Pd (MAX) and Ta MAX is required. This is graphically shown in the heat derating curve for easy understanding. The heat dissipation design is done in the following procedure.

- 1) The highest ambient temperature in the set Ta MAX is obtained.
- 2) The maximum loss PdMAX which varies the input/output conditions is obtained.

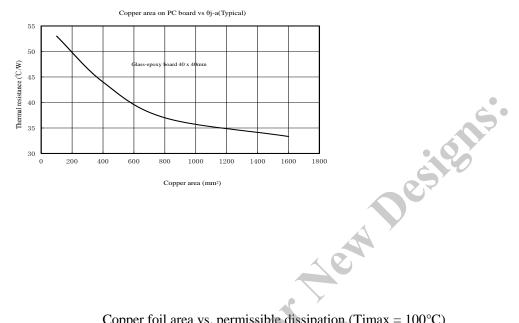
$$Pd = (V_{IN} - Vout) \times Iout$$

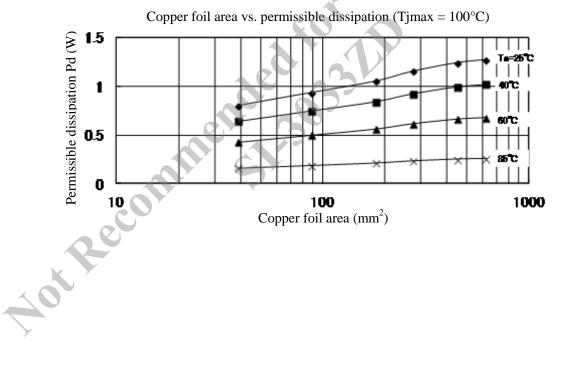
3) The area of copper foil is determined from the intersection point in the heat derating curve below shown.

#### SI – 3000KD derating curve

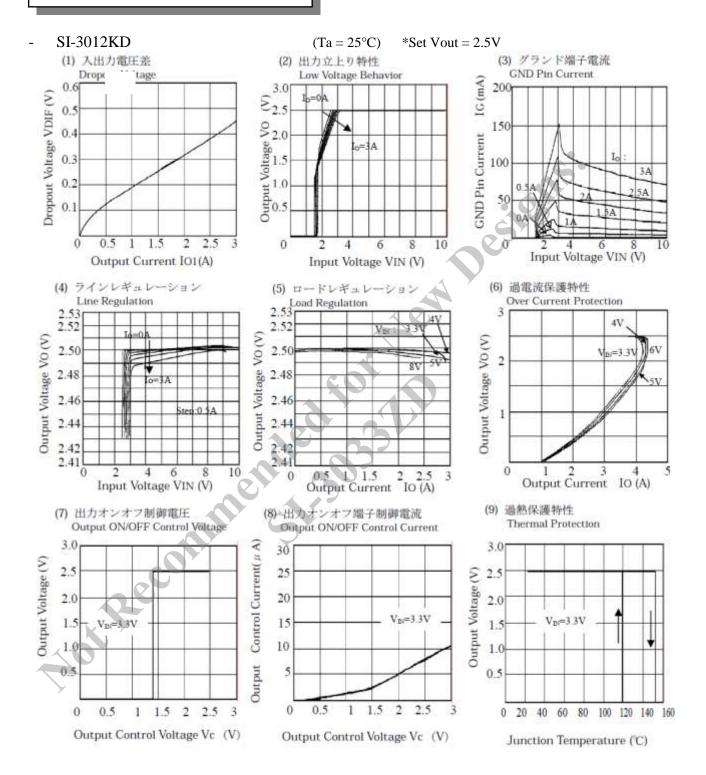


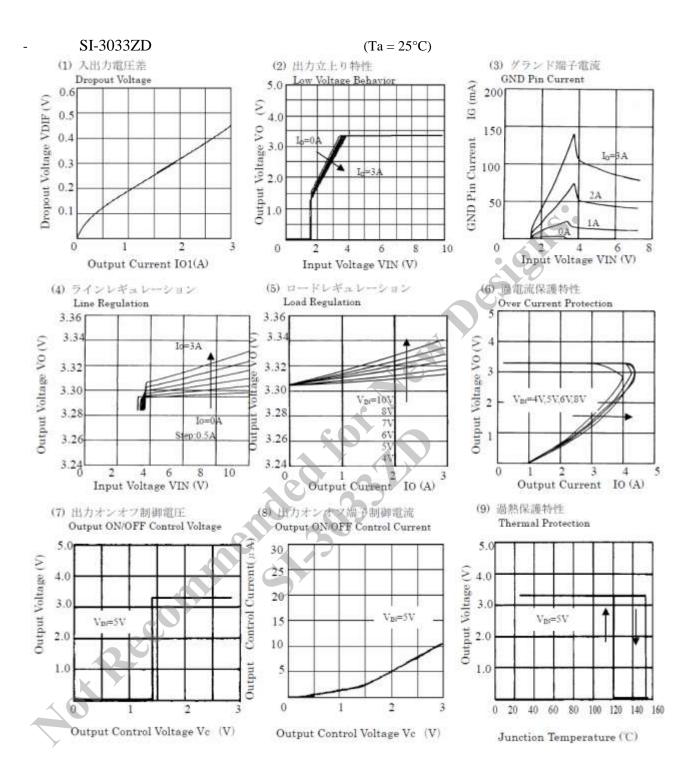
For reference information, the graph of copper foil area vs. thermal resistance between junction temperature and ambient temperature  $\theta$ j-a and the graph of copper foil area vs. permissible dissipation that both are in the single side copper foil board FR - 4 are shown below.





# 6. Typical Characteristics





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